

# Jeomoh Kim

## List of Publications by Year in descending order

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15  
papers

526  
citations

840776

11  
h-index

996975

15  
g-index

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all docs

15  
docs citations

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times ranked

665  
citing authors

| #  | ARTICLE  | IF  | CITATIONS |
|----|--|-----|-----------|
| 1  | p-i-p-i-n Separate Absorption and Multiplication Ultraviolet Avalanche Photodiodes. IEEE Photonics Technology Letters, 2018, 30, 181-184.  | 2.5 | 23        |
| 2  | Effect of lattice-matched InAlGaN electron-blocking layer on hole transport and distribution in InGaN/GaN multiple quantum wells of visible light-emitting diodes. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 1296-1301. | 1.8 | 3         |
| 3  | High-Responsivity GaN/InGaN Heterojunction Phototransistors. IEEE Photonics Technology Letters, 2016, 28, 2035-2038.   | 2.5 | 17        |
| 4  | Uniform and Reliable GaN &lt;italic>p-i-n</italic> Ultraviolet Avalanche Photodiode Arrays. IEEE Photonics Technology Letters, 2016, 28, 2015-2018.  | 2.5 | 26        |
| 5  | Radiative recombination in GaN/InGaN heterojunction bipolar transistors. Applied Physics Letters, 2015, 107, 242104.   | 3.3 | 2         |
| 6  | Al <sub>x</sub> Ga <sub>1-x</sub> N Ultraviolet Avalanche Photodiodes With Avalanche Gain Greater Than 10 <sup>5</sup> . IEEE Photonics Technology Letters, 2015, 27, 642-645.   | 2.5 | 38        |
| 7  | Comparison of AlGaIn ultraviolet avalanche photodiodes grown on free-standing GaN and sapphire substrates. Applied Physics Express, 2015, 8, 122202.   | 2.4 | 23        |
| 8  | Temperature-Dependent Resonance Energy Transfer from Semiconductor Quantum Wells to Graphene. Nano Letters, 2015, 15, 896-902.   | 9.1 | 12        |
| 9  | Temperature-Dependent Characteristics of GaN Homojunction Rectifiers. IEEE Transactions on Electron Devices, 2015, 62, 2679-2683.  | 3.0 | 19        |
| 10 | Direct periodic patterning of GaN-based light-emitting diodes by three-beam interference laser ablation. Applied Physics Letters, 2014, 104, 141105.   | 3.3 | 9         |
| 11 | Origins of unintentional incorporation of gallium in InAlN layers during epitaxial growth, part II: Effects of underlying layers and growth chamber conditions. Journal of Crystal Growth, 2014, 388, 143-149.   | 1.5 | 44        |
| 12 | Origins of unintentional incorporation of gallium in AlInN layers during epitaxial growth, part I: Growth of AlInN on AlN and effects of prior coating. Journal of Crystal Growth, 2014, 388, 137-142.   | 1.5 | 45        |
| 13 | Improved Hole Transport by $\text{In}_{1-x}\text{Ga}_x\text{N}$ Layer in Multiple Quantum Wells of Visible LEDs. IEEE Photonics Technology Letters, 2013, 25, 1789-1792.   | 2.5 | 2         |
| 14 | Efficiency droop due to electron spill-over and limited hole injection in III-nitride visible light-emitting diodes employing lattice-matched InAlN electron blocking layers. Applied Physics Letters, 2012, 101, .                                    | 3.3 | 80        |
| 15 | Improvement of peak quantum efficiency and efficiency droop in III-nitride visible light-emitting diodes with an InAlN electron-blocking layer. Applied Physics Letters, 2010, 96, .   | 3.3 | 183       |